ACTIVITY ID: 1903170031

## B.Sc. 6th Semester (Honours) Examination 2020

## **PHYSICS**

## (Nanomaterials and applications lab)

Paper: 604/DSE-4/P-7

**Course ID: 62427** 

Time: 1 Hour Full Marks: 10

> The figures in the margin indicate full marks. Students should write the answers in their own words as much as practicable. Answer all the questions.

- 1. Answer any *five* (05) questions: 2X5 = 10a) Name a metal that can be synthesized in its nano form using chemical route. Name the chemical used for the synthesis. Write the chemical reaction involved in this process. (1/2+1/2+1)b) What precautions should be taken for synthesis of metal nanoparticles employing chemical 2 route? c) Name four methods that can be employed to synthesize semiconductor nanoparticles.  $(\frac{1}{2}X4)$ d) Why capping agents are used to synthesize semiconductor nanoparticles? 2 e) Why the characterization of nanomaterials is necessary? Name two important characterization tools of nanomaterials and mention what type of information we may get using these tools. (1+1)  $(\frac{1}{2} X 4)$ f) Mention four important properties of carbon nano tubes (CNT). g) How the optical absorption data of nanomaterials can be used to estimate their sizes? 2 h) What do you mean by strong and weak confinement regime of nanomaterials? i) What do you mean by Surface Plasmon in connection to the optical properties of metal
- nanoparticles? What is Surface Plasmon Resonance (SPR)? (1+1)
- j) Why Surface Plasmon Resonance (SPR) is not important to the bulk metals but extremely important to the metal nanoparticles? 2

**Please Turn Over** 

k) How do the changes in (a) size and (b) shape of metal nanopaticles affect its Surface I	Plasmon
Resonance (SPR) characteristics?	(1+1)
1) How structural purity of a nanomaterial can be studied using X-ray diffraction data?	2
m) Explain the principle of estimating particle size from X-ray diffraction data.	2
n) What is a thin film capacitor? Why thin film capacitor is important in application	of nano
science?	(1+1)
o) Draw and explain the V-I characteristic of a PN diode manufactured by diffusing Al surface of N-type Si.	over the (1+1)